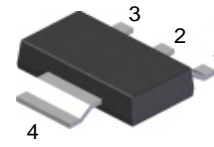


**Features**

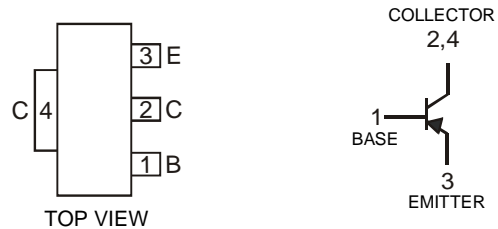
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZT5551)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 3)**



SOT-223

**Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic            | Symbol           | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage    | V <sub>CBO</sub> | -160  | V    |
| Collector-Emitter Voltage | V <sub>CEO</sub> | -150  | V    |
| Emitter-Base Voltage      | V <sub>EBO</sub> | -5.0  | V    |
| Collector Current         | I <sub>C</sub>   | -600  | mA   |

**Thermal Characteristics**

| Characteristic  | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation @T <sub>A</sub> = 25°C (Note 3)                       | P <sub>D</sub>                    | 1           | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 3) | R <sub>θJA</sub>                  | 125         | °C/W |
| Operating and Storage Temperature Range                                 | T <sub>j</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                       | Symbol               | Min            | Max           | Unit     | Test Condition   |
|--------------------------------------|----------------------|----------------|---------------|----------|--|
| <b>OFF CHARACTERISTICS (Note 4)</b>  |                      |                |               |          |  |
| Collector-Base Breakdown Voltage     | V <sub>(BR)CBO</sub> | -160           | —             | V        | I <sub>C</sub> = -100μA, I <sub>E</sub> = 0  |
| Collector-Emitter Breakdown Voltage  | V <sub>(BR)CEO</sub> | -150           | —             | V        | I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0  |
| Emitter-Base Breakdown Voltage       | V <sub>(BR)EBO</sub> | -5.0           | —             | V        | I <sub>E</sub> = -10μA, I <sub>C</sub> = 0   |
| Collector Cutoff Current             | I <sub>CBO</sub>     | —              | -50           | nA<br>μA | V <sub>CB</sub> = -120V, I <sub>E</sub> = 0<br>V <sub>CB</sub> = -120V, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C                                     |
| Emitter Cutoff Current               | I <sub>EBO</sub>     | —              | -50           | nA       | V <sub>EB</sub> = -3.0V, I <sub>C</sub> = 0  |
| <b>ON CHARACTERISTICS (Note 4)</b>   |                      |                |               |          |  |
| DC Current Gain                      | h <sub>FE</sub>      | 50<br>60<br>50 | —<br>240<br>— | —        | I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -5.0V<br>I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5.0V<br>I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5.0V |
| Collector-Emitter Saturation Voltage | V <sub>CE(SAT)</sub> | —              | -0.2<br>-0.5  | V        | I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA<br>I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA   |
| Base-Emitter Saturation Voltage      | V <sub>BE(SAT)</sub> | —              | -1.0          | V        | I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA<br>I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA   |
| <b>SMALL SIGNAL CHARACTERISTICS</b>  |                      |                |               |          |  |
| Output Capacitance                   | C <sub>obo</sub>     | —              | 6.0           | pF       | V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0   |
| Small Signal Current Gain            | h <sub>fe</sub>      | 40             | 200           | —        | V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA, f = 1.0kHz  |
| Current Gain-Bandwidth Product       | f <sub>T</sub>       | 100            | 300           | MHz      | V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA, f = 100MHz   |
| Noise Figure                         | NF                   | —              | 8.0           | dB       | V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -200μA, R <sub>S</sub> = 10Ω, f = 1.0kHz   |

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Measured under pulsed conditions. Pulse width = 300ms. Duty cycle ≤ 2%.

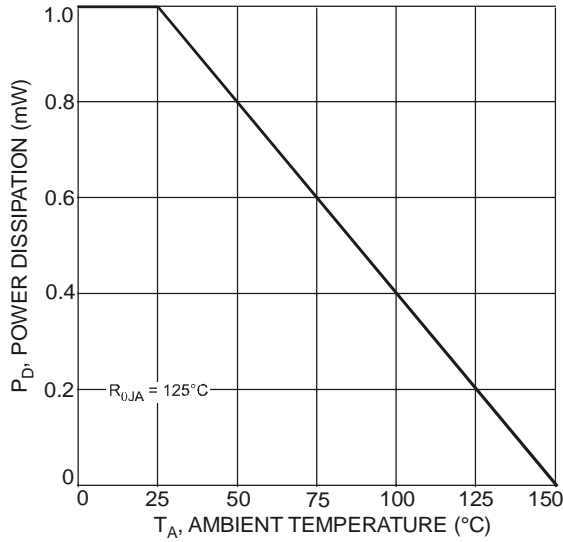


Fig. 1 Max Power Dissipation vs. Ambient Temperature

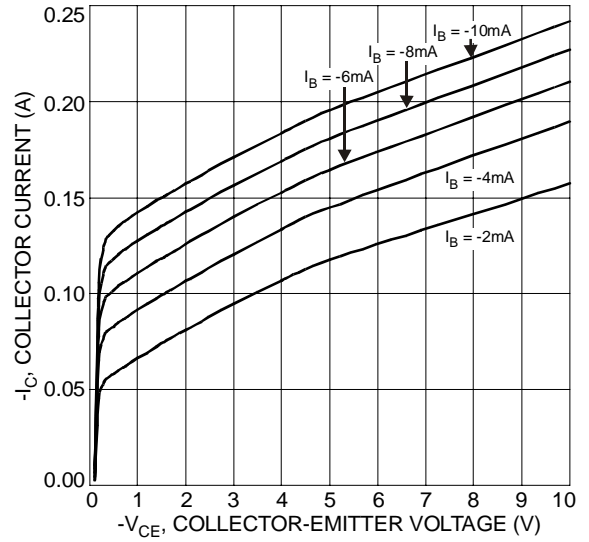


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

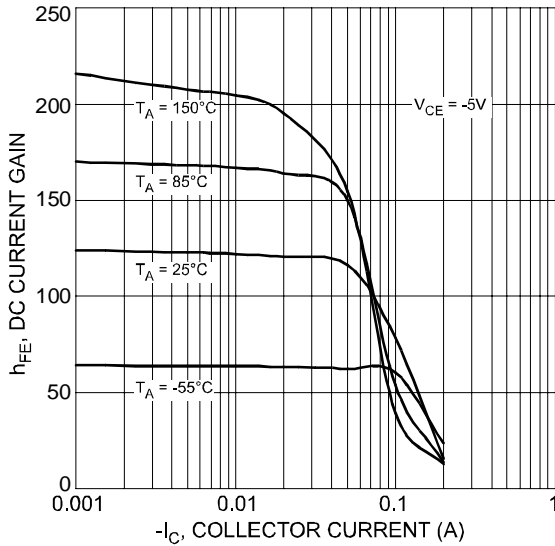


Fig. 3 Typical DC Current Gain vs. Collector Current

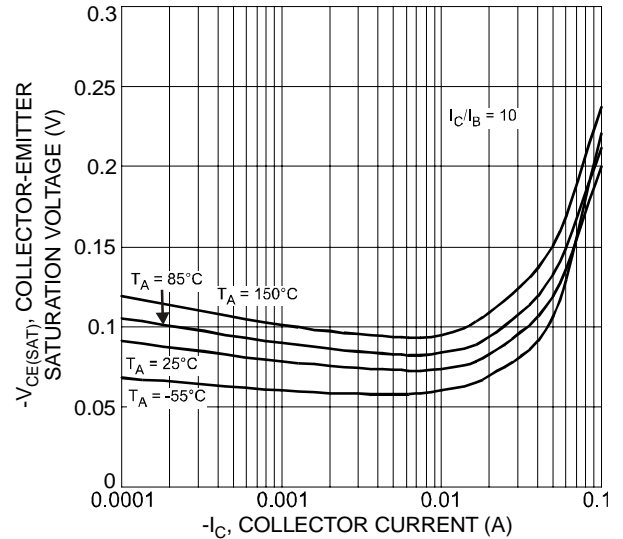


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

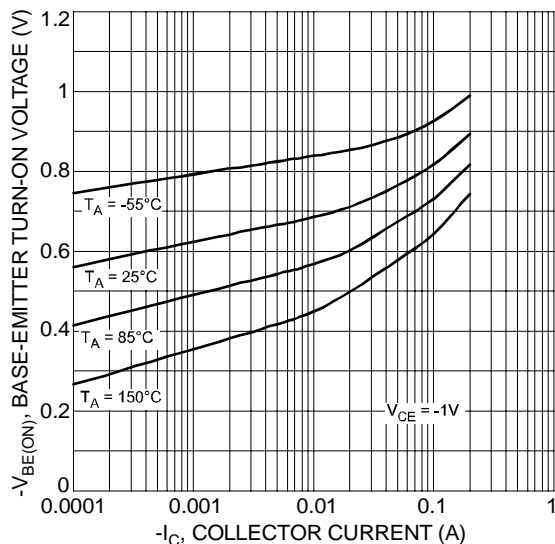


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

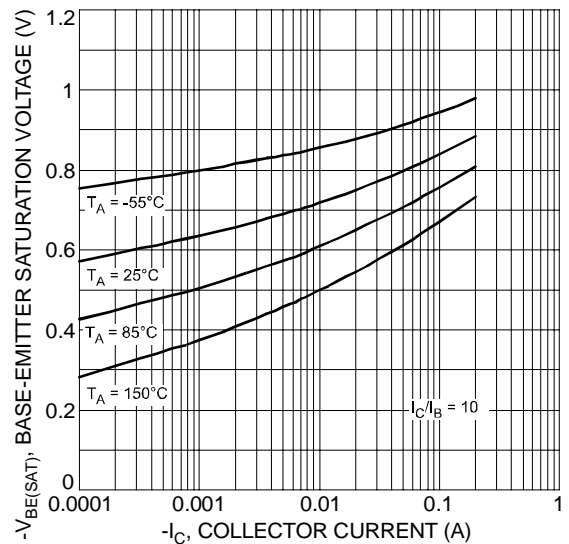


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

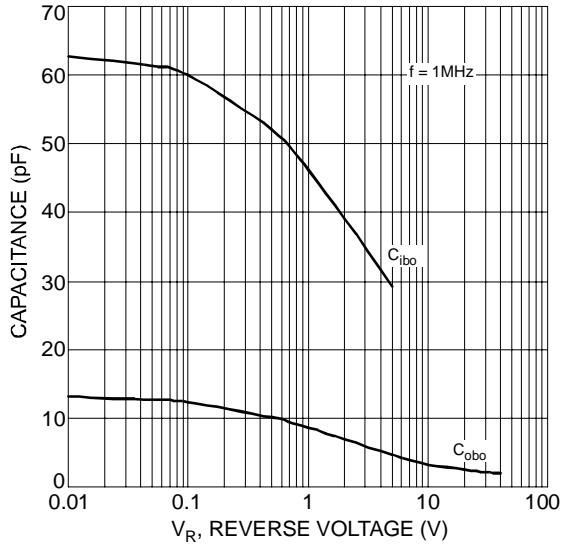


Fig. 7 Typical Capacitance Characteristics

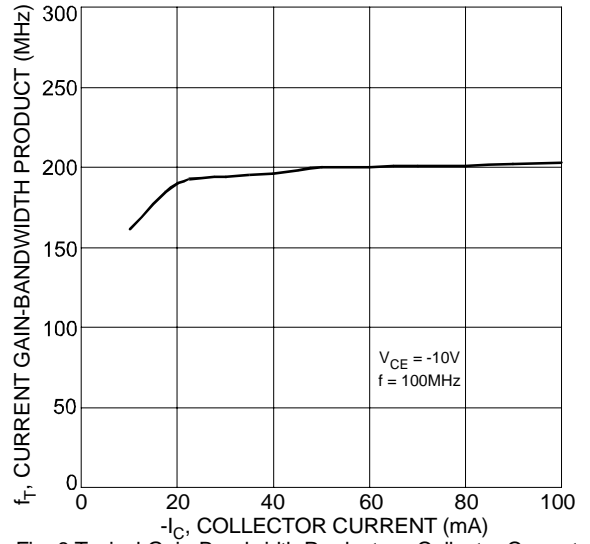


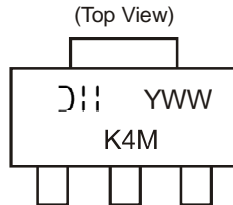
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

## Ordering Information (Note 5)

| Device     | Packaging | Shipping         |
|------------|-----------|------------------|
| DZT5401-13 | SOT-223   | 2500/Tape & Reel |

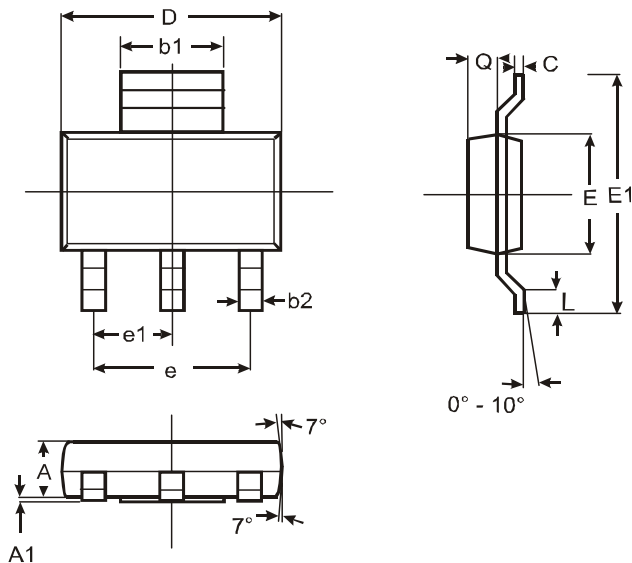
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



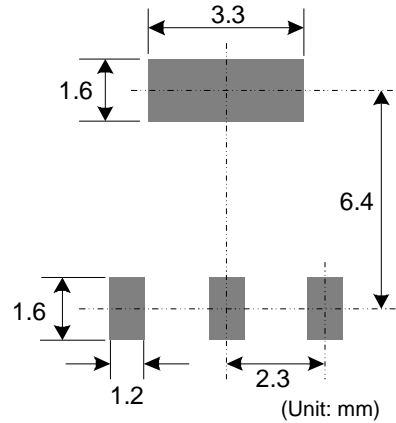
K4M = Product type marking code  
 DZ = Manufacturer's code marking  
 YWW = Date code marking  
 Y = Last digit of year ex: 7 = 2007  
 WW = Week code 01 - 52

## Package Outline Dimensions



| SOT-223              |       |      |      |
|----------------------|-------|------|------|
| Dim                  | Min   | Max  | Typ  |
| A                    | 1.55  | 1.65 | 1.60 |
| A1                   | 0.010 | 0.15 | 0.05 |
| b1                   | 2.90  | 3.10 | 3.00 |
| b2                   | 0.60  | 0.80 | 0.70 |
| C                    | 0.20  | 0.30 | 0.25 |
| D                    | 6.45  | 6.55 | 6.50 |
| E                    | 3.45  | 3.55 | 3.50 |
| E1                   | 6.90  | 7.10 | 7.00 |
| e                    | —     | —    | 4.60 |
| e1                   | —     | —    | 2.30 |
| L                    | 0.85  | 1.05 | 0.95 |
| Q                    | 0.84  | 0.94 | 0.89 |
| All Dimensions in mm |       |      |      |

## Suggested Pad Layout



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